



JCD30Y065A

SiC Schottky Diode

Rev.1.0

DESCRIPTION

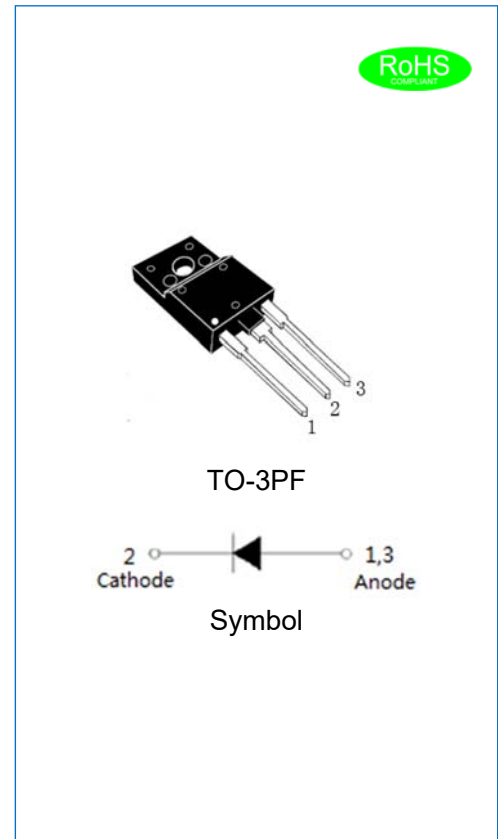
- ✧ 650V Schottky diode
- ✧ Zero reverse recovery current
- ✧ Zero forward recovery voltage
- ✧ High frequency operation
- ✧ Switching characteristics independent of temperature
- ✧ Fast switch
- ✧ Positive temperature coefficient of forward voltage (V_F)

BENEFIT

- ✧ Lower switching loss
- ✧ No thermal runaway in parallel devices
- ✧ Lower heatsink dependent
- ✧ Electrically isolated package
- ✧ Ceramic package provides 2500V isolation

APPLICATION

- ✧ Switch mode power supplies(SMPS)
- ✧ Boost diodes in PFC or DC/DC stages
- ✧ Free wheeling diodes in inverter stages
- ✧ AC/DC converters



ABSOLUTE MAXIMUM RATING (Rating at 25°C junction temperature unless otherwise specified.)

Parameter		Symbol	Value	Unit
Maximum repetitive peak reverse voltage		V_{RRM}	650	V
Maximum DC blocking voltage		V_{DC}	650	V
Average forward current	$T_C=80^{\circ}\text{C}$	$I_{F(AV)}$	30	A
Repetitive peak forward surge current	$t_P=10\text{ms}, T_C=25^{\circ}\text{C}$	I_{FRM}	200	A
Non-repetitive peak forward surge current	$t_P=10\text{ms}, T_C=25^{\circ}\text{C}$	I_{FSM}	240	A
Non-repetitive peak forward surge current	$T_C=25^{\circ}\text{C}, t_P=10\mu\text{s}, \text{Pulse}$	I_{FMax}	1600	A
Power dissipation	$T_C=25^{\circ}\text{C}$ $T_C=110^{\circ}\text{C}$	P_{tot}	283 123	W
Operating junction temperature range		T_j	-55 to +175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to +175	$^{\circ}\text{C}$

ISOLATION CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50Hz $\leq$ f $\leq$ 60Hz; RH $\leq$ 65%; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	Isolation capacitance	from cathode to external heatsink	-	10	-	pF

ELECTRICAL CHARACTERISTICS (Rating at 25°C junction temperature unless otherwise specified.)

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
Forward voltage	$I_F=30A, T_J=25^\circ C$	V_F	-	1.45	1.80	V
	$I_F=30A, T_J=175^\circ C$		-	1.95	2.40	
Reverse current	$V_R=650V, T_J=25^\circ C$	I_R	-	2	20	μA
	$V_R=650V, T_J=175^\circ C$		-	40	200	
Total capacitance	$V_R=0V, f=1MHz$	C	-	2050	-	pF
	$V_R=200V, f=1MHz$		-	162	-	
	$V_R=400V, f=1MHz$		-	137	-	
Total capacitance charge	$V_R=400V, T_J=25^\circ C$	Q_C	-	85	-	nC
Capacitance stored energy	$V_R=400V$	E_C	-	21	-	μJ

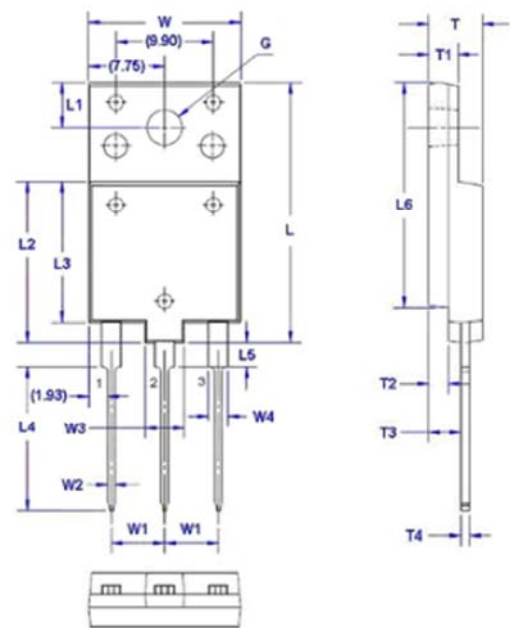
THERMAL CHARACTERISTICS

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{th(j-c)}$	Junction to case	-	-	2.2	$^\circ C/W$

ORDERING INFORMATION

J	CD	30	Y	065	A
JieJie Microelectronics Co., Ltd	SiC Schottky Diode	$I_F(AV)=30A$	Y: TO-3PF	$V_{RRM}:650V$	Version A

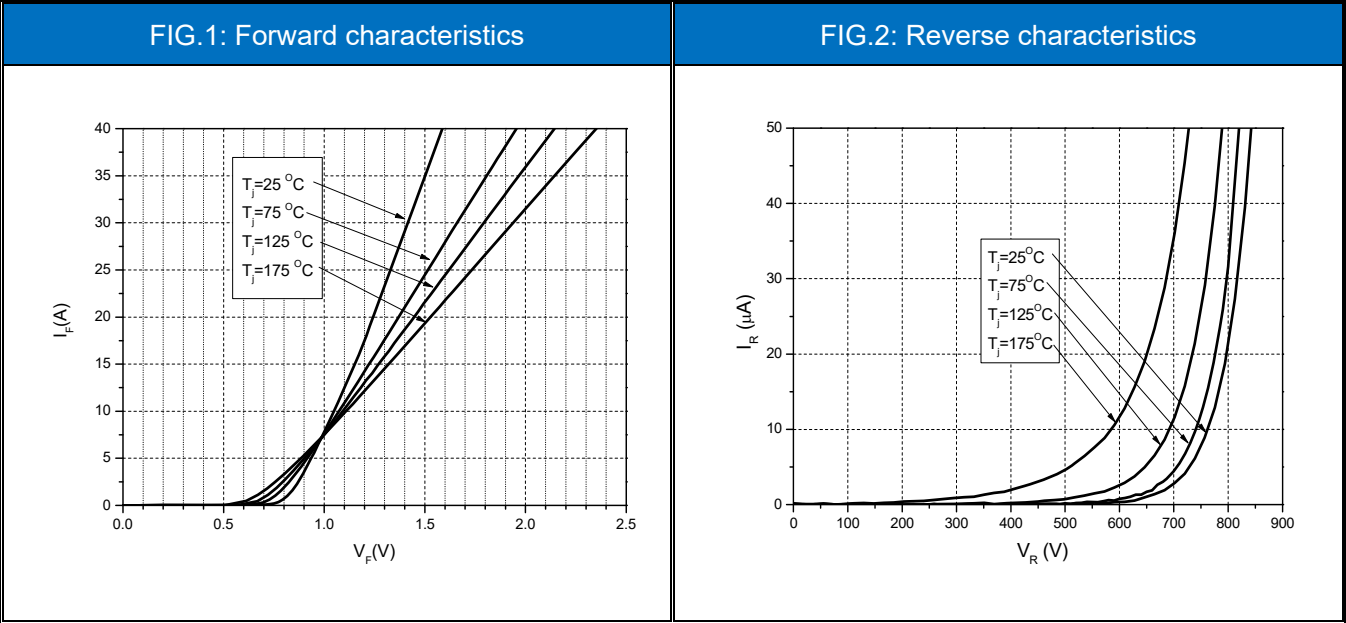
PACKAGE MECHANICAL DATA



(Unit: mm)

Symbol	Dimension		Symbol	Dimension	
	Min	Max		Min	Max
W	15.30	15.70	L4	14.60	15.00
W1	5.15	5.75	L5	2.30	2.70
W2	0.65	0.95	L6	22.80	23.20
W3	3.80	4.20	T	5.30	5.70
W4	1.80	2.20	T1	2.80	3.20
L	26.30	26.70	T2	1.80	2.20
L1	4.40	4.60	T3	3.10	3.50
L2	16.30	16.70	T4	0.80	1.10
L3	14.30	14.70	G(Φ)	3.40	3.80

CHARACTERISTICS CURVE



CHARACTERISTICS CURVE

FIG.3: Capacitance vs. reverse voltage

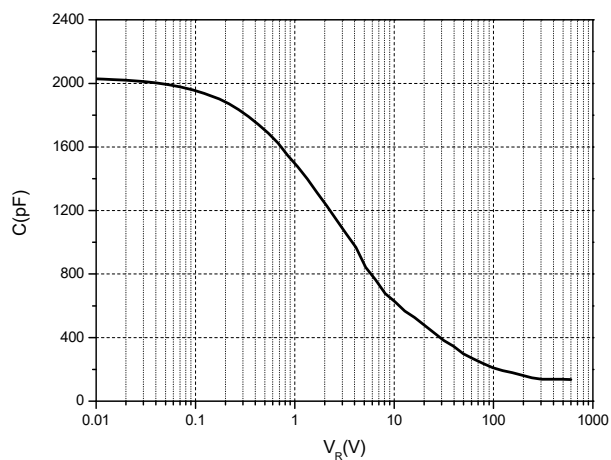


FIG.4: Capacitance charge vs. reverse voltage

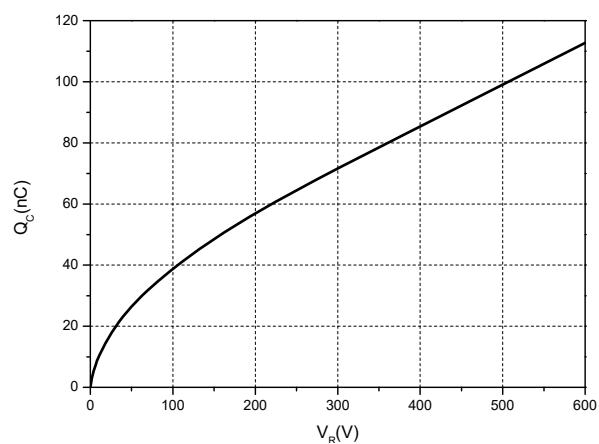


FIG.5: Capacitance stored energy

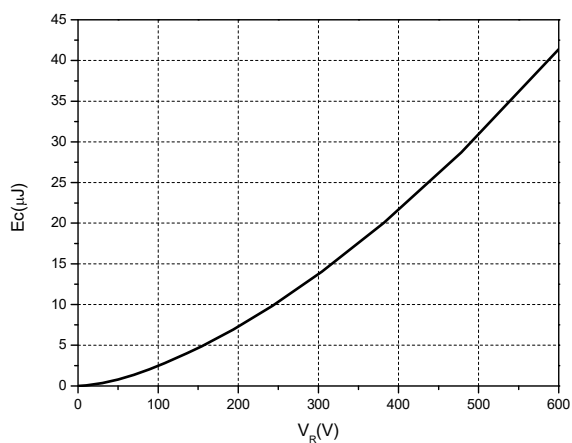
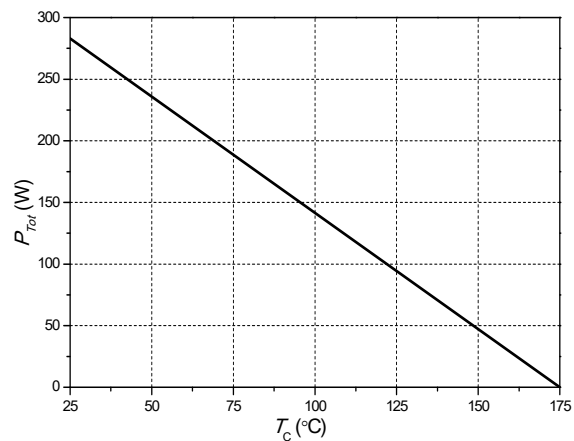


FIG.6: Power derating



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